



# 2SK3979 — N-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- Low ON-resistance.
- Ultrahigh-speed switching.

### Specifications

**Absolute Maximum Ratings** at  $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	$V_{DSS}$		200	V
Gate-to-Source Voltage	$V_{GSS}$		$\pm 30$	V
Drain Current (DC)	$I_D$		6	A
Drain Current (Pulse)	$I_{DP}$	$PW \leq 10\mu\text{s}$ , duty cycle $\leq 1\%$	24	A
Allowable Power Dissipation	$P_D$		1	W
		$T_c=25^\circ\text{C}$	20	W
Channel Temperature	$T_{ch}$		150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** at  $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}$ , $V_{GS}=0\text{V}$	200			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=200\text{V}$ , $V_{GS}=0\text{V}$			1	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 24\text{V}$ , $V_{DS}=0\text{V}$			$\pm 1$	$\mu\text{A}$
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}$ , $I_D=1\text{mA}$	2.0		3.2	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}$ , $I_D=3\text{A}$	2.1	3.5		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=3\text{A}$ , $V_{GS}=10\text{V}$		320	450	$\text{m}\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=20\text{V}$ , $f=1\text{MHz}$		1090		pF
Output Capacitance	$C_{oss}$	$V_{DS}=20\text{V}$ , $f=1\text{MHz}$		85		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=20\text{V}$ , $f=1\text{MHz}$		35		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		17.5		ns
Rise Time	$t_r$	See specified Test Circuit.		26		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		50		ns
Fall Time	$t_f$	See specified Test Circuit.		42		ns

Marking : K3979

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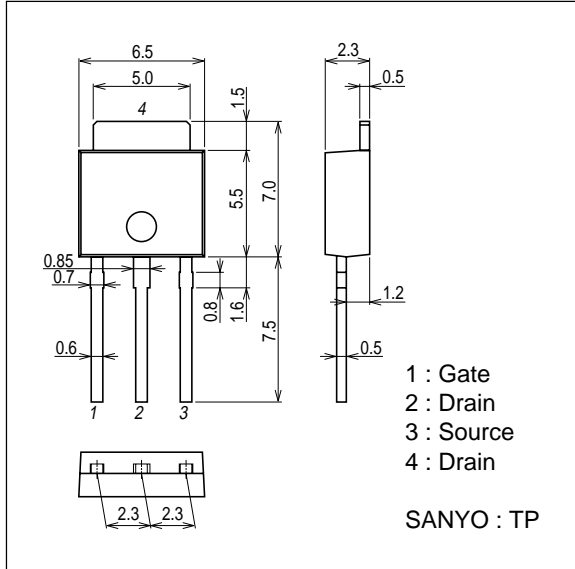
# 2SK3979

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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V <sub>DS</sub> =100V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		18.2		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =100V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		8.0		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =100V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		7.0		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =6A, V <sub>GS</sub> =0V		0.86	1.2	V

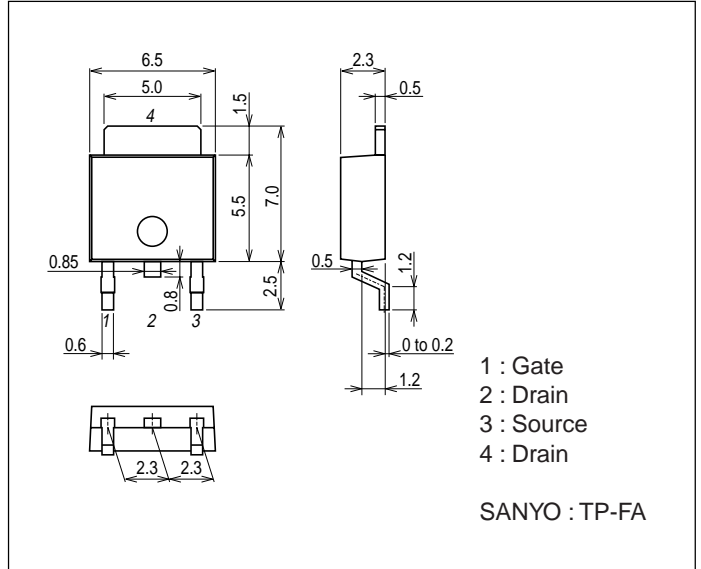
## Package Dimensions

unit : mm  
7518-004

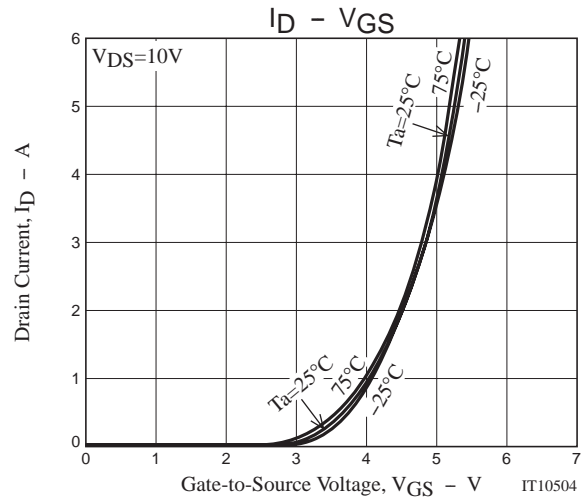
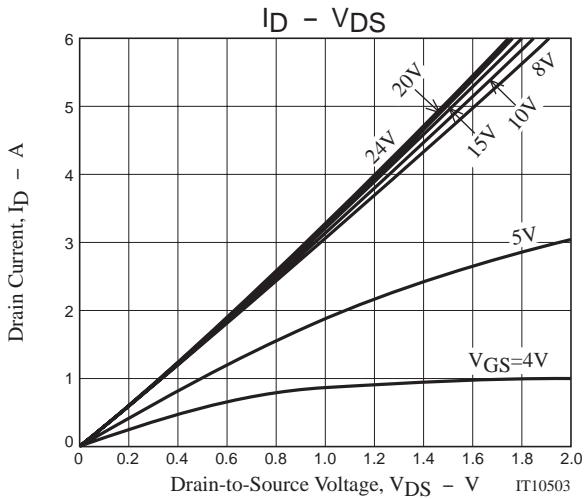
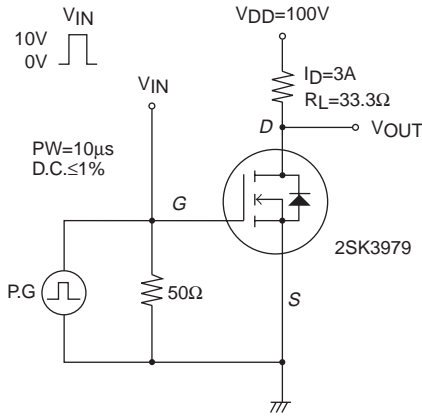


## Package Dimensions

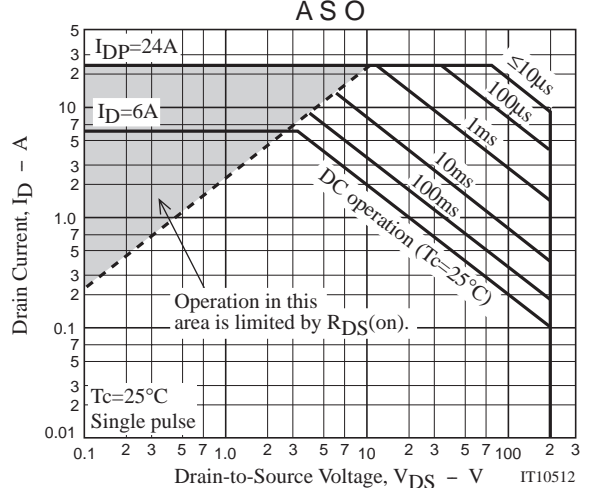
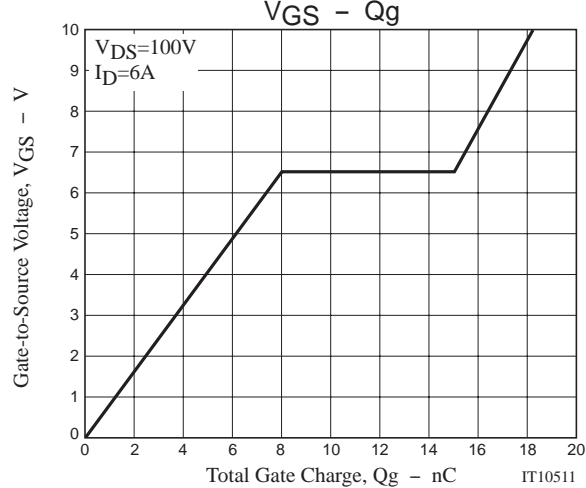
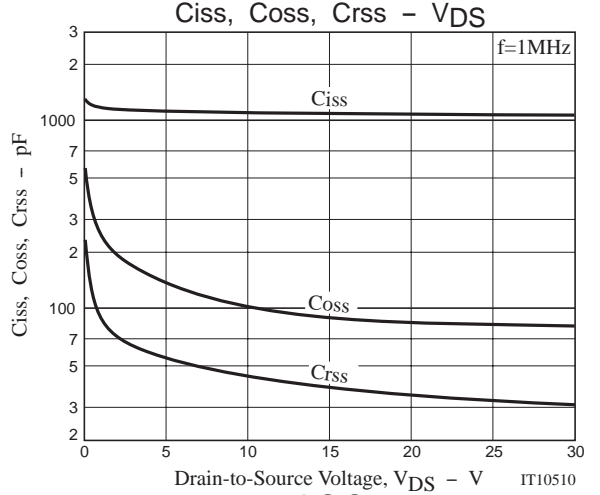
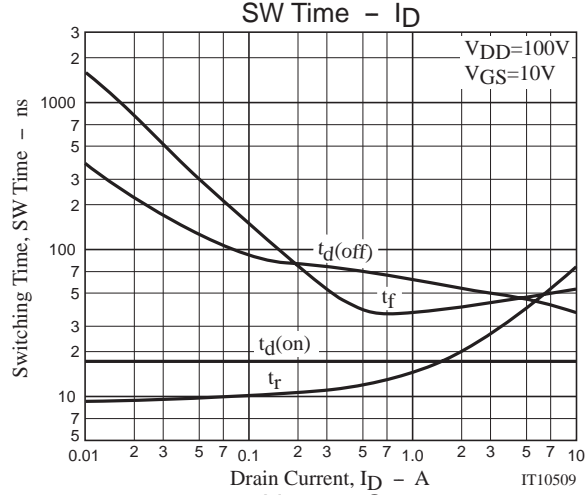
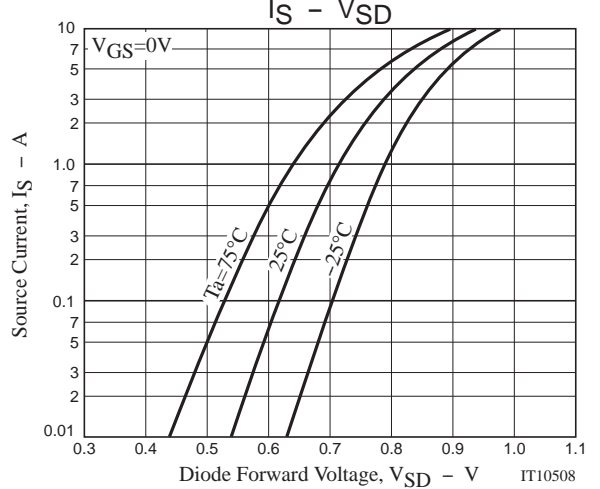
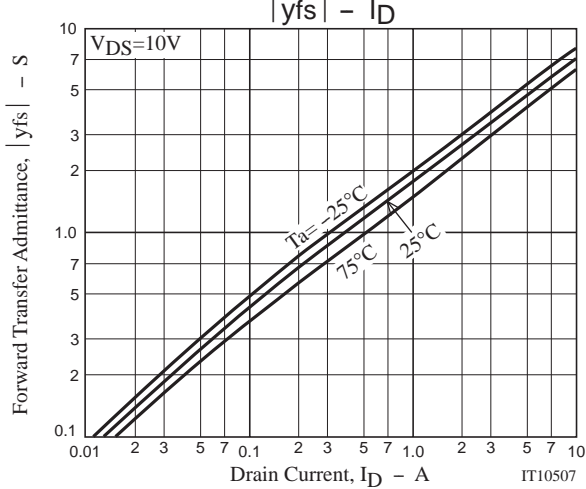
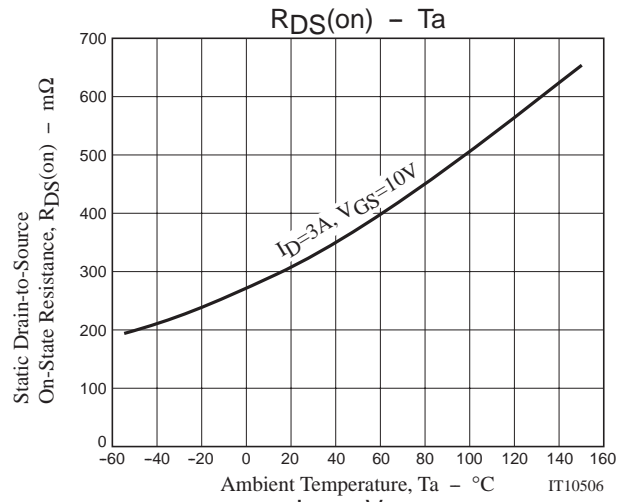
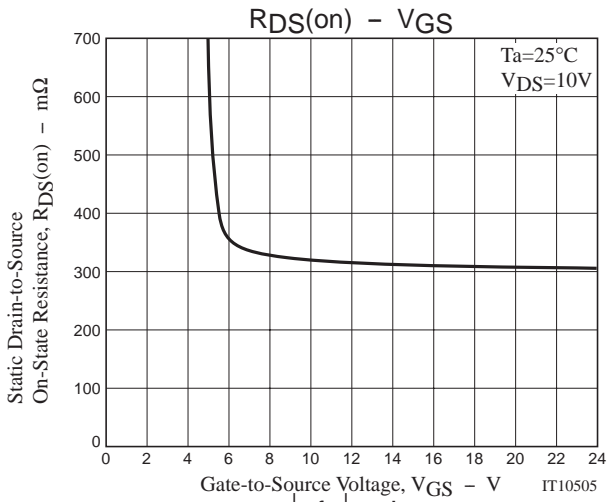
unit : mm  
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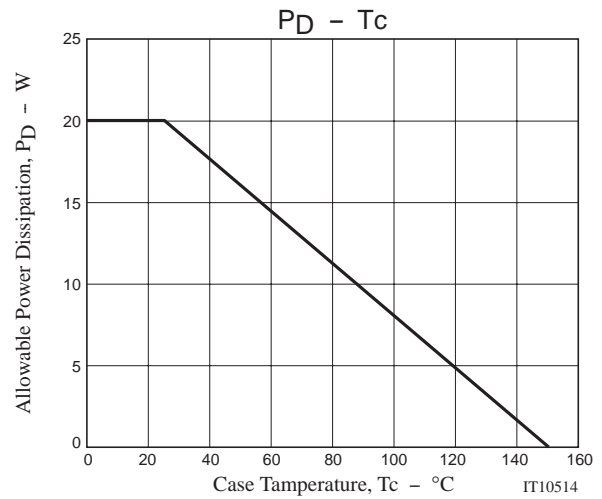
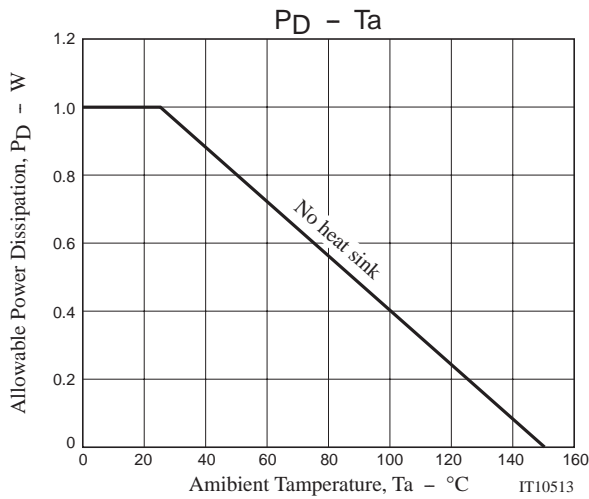


## Switching Time Test Circuit



# 2SK3979





Note on usage : Since the 2SK3979 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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